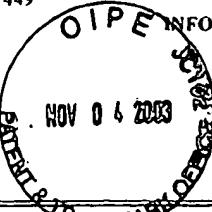
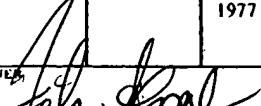


Form PTO-1449 		Docket Number (Optional) 068758.0102	Application Number 097786,022 10/633044
		Applicant Deboy et al.	
		Filing Date 04/22/99	Group Art Unit:

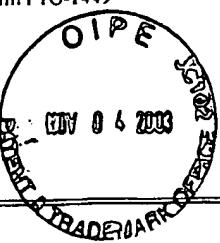
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
PT	3,171,068	02/23/65	Denkewalter et al.	317	234	10/19/60
	3,925,803	12/09/75	Kobayashi	357	22	07/12/73
	3,961,356	06/01/76	Okuhura et al.	357	50	10/31/74
	4,003,072	01/11/77	Matsushita et al.	357	52	11/01/74
	4,055,884	11/01/77	Jamboikar	29	571	12/13/76
	4,072,975	02/07/78	Ishtiani	357	23	04/22/77
	4,101,922	07/18/78	Tihanyi	357	23	03/09/77
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	4,345,265	08/17/82	Blanchard	357	23	04/14/80
	4,366,495	12/28/82	Goodman et al	357	23	08/06/79
	4,376,286	03/08/83	Lidow et al.	357	23	02/09/81
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	Translation	
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EP 0 053 854 B1	16.06.82	EPO	H01L	29/06	x	
GB 2 089 118 A	16.02.82	UK	H01L	29/78	x	
EP 0 069 429 A2	12.01.83	EPO	H01L	29/78	x	
EP 0 447 873 A2	01.04.92	EPO	H01L	29/784	x	
DE 43 09 764 A1	25.03.93	Germany	H01L	29/784		x
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		1967	A.S. Grove: "Physics and Technology of Semiconductor Devices" p 78-83
		1976	B. Jayant Baliga, Sorab K. Ghandi: "Analytical Solutions for the Breakdown Voltage of Abrupt Cylindrical and Spherical Junctions" (p 739-744)
		1977	Richard F. David: "Computerized Thermal Analysis of Hybrid Circuits" 27th Electronics Components Conference, May 16-18 1977 (p 324-332)
EXAMINER 	DATE CONSIDERED 7/16/04		

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)				Docto Number (Optional)	Application Number	
				068758.0102	09786,922 10/633044	
				Applicant Debey et al.		
				Filing Date 04/22/99	Group Art Unit:	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
X	4,404,575	09/13/83	Nishizawa	357	22	05/03/82
	4,417,385	11/29/83	Temple	29	571	09/09/82
	4,561,003	12/24/85	Tihanyi et al.	357	23.4	04/13/84
	4,593,302	06/03/86	Lidow et al	357	23.4	08/18/80
	4,748,103	05/31/88	Hollinger	430	314	03/21/66
	4,754,310	06/28/88	Coe	357	13	12/04/84
	4,775,881	10/04/88	Ploss et al	357	30	02/13/87
	4,777,149	10/11/88	Tanabe et al.	437	142	12/22/87
	4,895,810	01/23/90	Meyers et al.	431	41	05/17/88
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Tradition	
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	EP 0 772 244 A1	07.05.97	EPO	H01L	29/78	x
	DE 196 04 043 A1	5.2.96	Germany	H01L	29/78	x
	WO 97/29518	14.08.97	PCT	H01L	29/78	x
	DE 196 04 044 A1	5.2.97	Germany	H01L	29/78	x
	WO 97/35346	25.09.97	PCT	H01L	29/78	x
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	DE 197 30 759 C1	17.7.97	Germany	H01L	29/78	x
	WO 99/04437	28.01.99	PCT	H01L	29/78	x
	WO 99/23703	14.05.99	PCT	H01L	29/06	x
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<b>OTHER DOCUMENTS</b> (Including Author, Title, Date, Pertinent Pages, Etc.)						
	IEEE	1977	Vinson C. Alwin, David H. Navon, Luke J. Turgeon: "Time-Dependent Carrier Flow in a Transistor Structure Under Nonisothermal Conditions" (p 1297-1304)			
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	IEEE	1979	J.A. Appel, H.M.J. Vaes: "High Voltage Thin Layer Devices (Resurf Devices)" (p 1384-1387)			
EXAMINER <i>John Kaval</i>				DATE CONSIDERED	7/16/04	
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						

Form PTO-449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)				Docket Number (Optional) 068758.0102	Application Number 09/786,022 10/633 044
				Applicant Debey et al.	
				Filing Date 04/22/99	Group Art Unit: Group Art Unit:

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
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	4,926,226	05/15/90	Heremans et al.	357	27	09/06/88
	4,941,026	07/10/90	Temple	357	23.4	08/26/88
	4,974,059	11/27/90	Kinzer	357	23.4	08/28/89
	4,975,782	12/04/90	Bauer	357	38	02/22/89
	4,994,871	02/19/91	Chang et al.	357	23.4	12/02/88
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	5,010,025	04/23/91	Solomon	437	29	04/03/89
	5,019,522	05/28/91	Meyer et al.	437	29	01/02/90
	5,045,903	09/03/91	Meyer et al.	357	23.4	11/16/89
	5,072,269	12/10/91	Heida	357	23.6	03/15/89
	5,089,434	02/18/92	Hollinser	437	41	01/22/90
EXAMINER	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	Translation YES NO
	WO99/36961	22.07.99	PCT	H01L	23/48	x
	DE 197 36 981C2	25.8.97	Germany	H01L	29/78	x
	EP 0 939 446 A1	01/09/99	EPO	H01L	29/08	x
	WO 00/14807	16.03.00	PCT	H01L	29/78	x
	DE 198 40 032 C1	2.9.98	Germany	H01L	29/78	x
	WO 99/62123	02.12.99	PCT	H01L	29/861	x
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IEEE	1979	Chenming Hu article, "Optimum Doping Profile for Minimum Ohmic Resistance and High-Breakdown Voltage"

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

DATE CONSIDERED

2/16/00

Form PTO-146 O P E PATENT & TRADEMARK OFFICE NOV 8 2003		INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		Docket Number (Optional) 068758.0102	Application Number 09/786,022 10/633,046
				Applicant Deboy et al.	
				Filing Date 04/22/99	Group Art Unit:

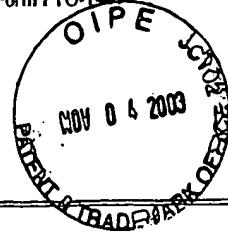
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
R	5,126,807	06/30/92	Baba et al.	357	23.4	06/12/91
	5,182,234	01/26/93	Meyer	437	233	07/26/91
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	5,283,201	02/01/94	Tsang et al.	437	31	08/07/92
	5,340,315	07/04/95	Rumennik	257	331	10/11/94
	5,438,215	08/01/95	Tihanyi	257	401	03/25/94
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	Translation	
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WO 00/02250	13.01.00	PCT	H01L	29/10		x
EP 0 973 203 A2	19.01.00	EPO	H01L	29/06		x
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	1979	IEDM Technical Digest excerpt (p. 239, 241)	
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UMI	December 1981	Richard A. Blanchard: "Optimization of Discrete High Power MOS Transistors"	

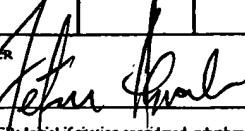
EXAMINER <i>Felicia Blake</i>	DATE CONSIDERED <i>7/16/04</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)				Docto Number (Optional)	Application Number		
				068758.0102	09786,022- 10/633044		
				Applicant Deboy et al.			
				Filing Date 04/22/99	Group Art Unit:		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE	
PA	5,473,180	12/05/95	Ludikhuize	257	336	07/11/94	
	5,559,353	09/24/96	Risch et al.	257	334	11/01/94	
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	US2001/0050549		Deboy et al.	323	313	03/12/01	
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	Translation		
					YES	NO	
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IEEE	1981	J.P. Stengl, H. Strack, J. Tihanyi: "Power MOS Transistors for 1000 V Blocking Voltage" (p 422-425)					
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✓ J	IEEE	1984	Akio Nakagawa, David H. Navon: "A Time- and Temperature-Dependent 2-D Simulation of the GTO Thyristor Turn-Off Process" (p 1156-1163)				
EXAMINER Initial if citation considered, whether or not citation is in conformance with MPEP §609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.				DATE CONSIDERED 7/16/04			

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)				Docket Number (Optional)	Application Number	
				068758.0102	09786,022 10/633044	
				Applicant Debay et al.		
				Filing Date 04/22/99	Group Art Unit:	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME		CLASS	SUB-CLASS
	DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB-CLASS
<b>OTHER DOCUMENTS</b> (Including Author, Title, Date, Pertinent Pages, Etc.)						
	IEEE	1984	Chenming Hu, Min-Hwa Chi, Vikram M. Patel: "Optimum Designs of Power MOSFET's" (p 1693-1700)			
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EXAMINER				DATE CONSIDERED 7/16/04		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)				Docket Number (Optional) 068758.0102	Application Number 09/786,022- 10/633044	
				Applicant Deboy et al.		
				Filing Date 04/22/99	Group Art Unit:	
<b>U.S. PATENT DOCUMENTS</b>						
<b>EXAMINER INITIAL</b> <i>PA</i>	<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB- CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>
						Translation _____
	<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>COUNTRY</b>	<b>CLASS</b>	<b>SUB- CLASS</b>	<b>YES</b> <b>NO</b>
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>						
	IEEE	Oct. 1988	Zahir Parpia, C. Andre T. Salama, Robert A. Hadaway, "A CMOS-Compatible High-Voltage IC Process" (p 1687-1694)			
	Chinese Journal of Semiconductors	1989	Chen Xingbi, Li Zhaoji, Li Zhongmin: "Breakdown Voltage of Cylindrical Boundary Abrupt Junctions" (p 463-465)			
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		1991	Article by Xing-Bi Chen presented at 2 <sup>nd</sup> German-Chinese Electronics Week Congress, Shanghai, China.			
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		1998	X.B. Chen et al., "Theory of a novel voltage-sustaining layer for power devices" (from Microelectronics Journal)			
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		July 1998	Steve Bush, "Five-fold resistance cut for high-voltage FETs"			
<b>EXAMINER</b> <i>Peter A. Deboy</i>				<b>DATE CONSIDERED</b> <i>7/10/00</i>		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						

<p style="text-align: center;">INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)</p>				Digital Number (Optional)	Application Number			
				068758.0102	09786,022- 10/633045P			
				Applicant Deboy et al.				
				Filing Date 04/22/99	Group Art Unit:			
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME		CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE	
	DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB-CLASS	Trademarks	
OTHER DOCUMENTS				(Including Author, Title, Date, Pertinent Pages, Etc.)				
Pp		1998	Lorenz et al. article, "Improved MOSFET An Important Milestone Toward a New Power MOSFET Generation" featured in PCIM					
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				DATE CONSIDERED			7/16/04	
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**INFORMATION  
DISCLOSURE  
CITATION**  
PTO-1449

Customer Number:  
**26615**

ATTORNEY's Dkt No.  
**H1174**

APPLICATION NO.  
**Unassigned**

APPLICANT(S)  
**Chih-Yuh Yang et al.**

FILING DATE  
**August 4, 2003**

GROUP  
**Unassigned**

**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

<i>FD</i>	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.
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<i>TAA</i>	Co-pending U.S. Application Serial Number 10/348,758 filed January 23, 2003 entitled, "GERMANIUM MOSFET DEVICES AND METHODS FOR MAKING SAME," Judy Xilin An et al., 22 page specification, 29 sheets of drawings.

EXAMINER

*Chih-Yuh Yang*

DATE CONSIDERED

*7/20/04*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).



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SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION</b> <small>PTO-1449</small>		<b>ATTORNEY'S DKT No.</b> <b>H1174</b>	<b>APPLICATION NO.</b> <b>10/633,034</b>
<b>Customer Number</b> <b>26615</b>		<b>APPLICANT(S)</b> <b>Chih-Yuh Yang et al</b>	
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## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

*[Handwritten mark]* U.S. Patent Application Publication No. US 2003/0113970 A1 ; June 19, 2003; Fried et al.  
*[Handwritten mark]* U.S. Patent Application Publication No. US 2003/0042531 A1; March 6, 2003; Lee et al.

EXAMINER <i>John Brink</i>	DATE CONSIDERED <i>7/20/04</i>
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